



60V N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
60V	8.3mΩ @ V _{GS} = 10V	40.6A
	12.5m Ω @ V _{GS} = 4.5V	33.1A

Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, making it ideal for high-efficiency power management applications

- Backlighting
- Power Management Functions
- DC-DC Converters

Features

- 100% Unclamped Inductive Switching (UIS) Test in Production— Ensures More Reliable and Robust End Application
- Low On-Resistance
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Wettable Flank for Improved Optical Inspection
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.

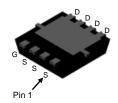
https://www.diodes.com/quality/product-definitions/

Mechanical Data

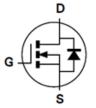
- Case: PowerDI[®]3333-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.072 grams (Approximate)

PowerDI3333-8 (SWP) (Type UX)





Top View Bottom View



Equivalent Circuit

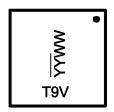
Ordering Information (Note 4)

Part Number	Case	Packaging
DMT69M5LFVW-7	PowerDI3333-8 (SWP) (Type UX)	2000/Tape & Reel
DMT69M5LFVW-13	PowerDI3333-8 (SWP) (Type UX)	3000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



 \overline{YY} = Product Type Marking Code \overline{YY} WW = Date Code Marking \overline{YY} = Last Two Digits of Year (ex: 19 = 2019) WW = Week Code (01 to 53)



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	VDSS	60	V	
Gate-Source Voltage	V _{GSS}	±20	V	
	Tc = +25°C	ΙD	40.6	A
Ocaliana Preis Oceana (Nata 5) V	Tc = +70°C		32.5	
Continuous Drain Current (Note 5) Vss = 10V	T _A = +25°C	ID	14.8	А
	T _A = +70°C		11.9	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	160	Α	
Maximum Continuous Body Diode Forward Current (Note 5)	Is	40	Α	
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%	I _{SM}	160	А	
Avalanche Current, L = 0.1mH	las	27.4	A	
Avalanche Energy, L = 0.1mH	Eas	37.5	mJ	

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5) $T_A = +25$ °C		P _D	2.74	W
Thermal Resistance, Junction to Ambient (Note 5)	R _θ JA	45.6	°C/W	
Total Power Dissipation (Note 6) $T_C = +25^{\circ}C$		P _D	20.5	W
Thermal Resistance, Junction to Case (Note 6)		R _θ JC	6.1	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

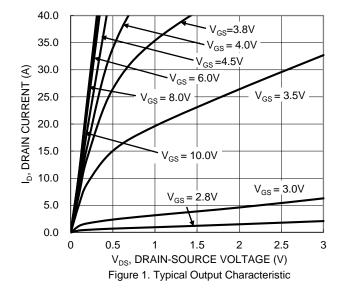
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	60	_	_	V	$V_{GS} = 0V, I_{D} = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 48V, V_{GS} = 0V$	
Gate-Source Leakage	Igss	_	_	±100	nA	$V_{GS} = \pm 20V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	Vgs(TH)	1.4	_	2.5	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance		_	6.2	8.3	mΩ	$V_{GS} = 10V, I_{D} = 13.5A$	
Static Dialii-Source Off-Resistance	RDS(ON)	_	9.2	12.5		$V_{GS} = 4.5V, I_D = 11.5A$	
Diode Forward Voltage	VsD	_	8.0	1.2	V	$V_{GS} = 0V, I_{S} = 13.5A$	
DYNAMIC CHARACTERISTICS (Note 8)	DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	Ciss	_	1406	_	pF	, , , , , , , , , , , , , , , , , , ,	
Output Capacitance	Coss	_	540	_	pF	$V_{DS} = 30V, V_{GS} = 0V,$ -f = 1MHz	
Reverse Transfer Capacitance	Crss	_	52	_	pF	1 – 1101112	
Gate Resistance	Rg	_	1.85	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 10V)	Qg	_	28.4	_	nC		
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	15.4	_	nC	\/ 20\/ I- 42.5A	
Gate-Source Charge	Qgs	_	2.4	_	nC	V _{DS} = 30V, I _D = 13.5A	
Gate-Drain Charge	Qgd	_	9.0	_	nC		
Turn-On Delay Time	tD(ON)	_	10.5	_	ns	$V_{DD} = 30V, V_{GS} = 10V,$ $R_g = 6\Omega, I_D = 13.5A$	
Turn-On Rise Time	t _R	_	49.0	_	ns		
Turn-Off Delay Time	t _{D(OFF)}	_	30.9	_	ns		
Turn-Off Fall Time	tF	_	79.5	_	ns		
Body Diode Reverse Recovery Time	t _{RR}	_	26.7	_	ns	I _F = 13.5A, di/dt = 300A/µs	
Body Diode Reverse Recovery Charge	Qrr	_	44.8	_	nC		

5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

^{6.} Thermal resistance from junction to soldering point (on the exposed drain pad).

^{7.} Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.





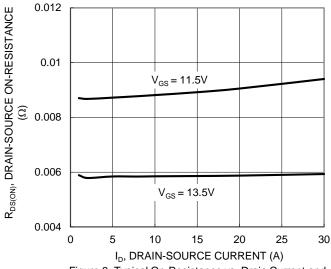


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

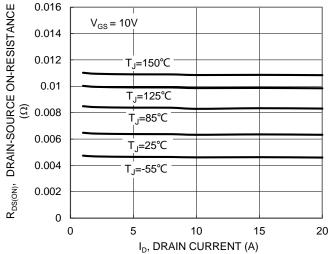


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

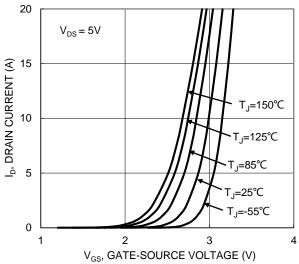


Figure 2. Typical Transfer Characteristic

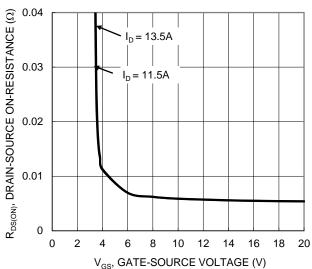


Figure 4. Typical Transfer Characteristic

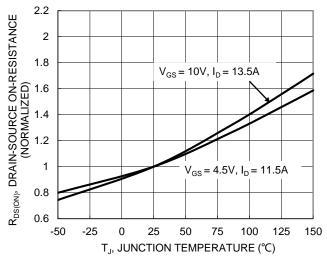
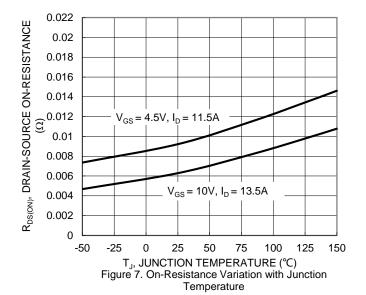
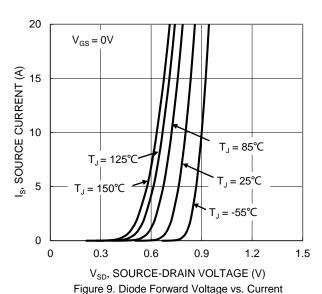
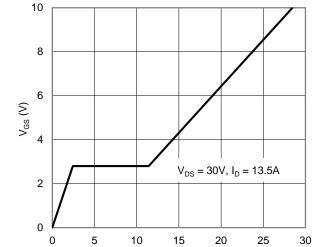


Figure 6. On-Resistance Variation with Junction Temperature

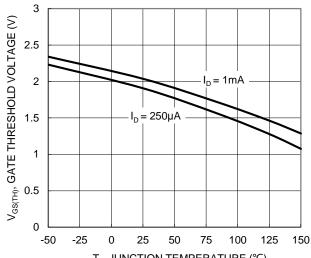




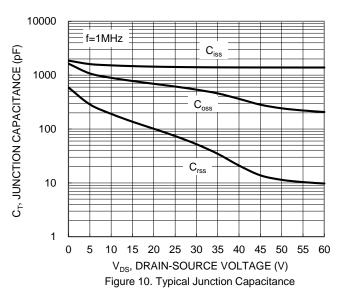




Qg (nC) Figure 11. Gate Charge



T_J, JUNCTION TEMPERATURE (°C) Figure 8. Gate Threshold Variation vs. Junction Temperature



1000 R_{DS(ON)} Limited 100 ID, DRAIN CURRENT (A) 10 =100µs 1 =100ms $T_{J(Max)} = 150^{\circ}C$ $T_C = 25^{\circ}C$ Single Pulse **DUT** on Infinite Heatsink $V_{GS} = 10V$ 0.01 0.1 10 100 V_{DS} , DRAIN-SOURCE VOLTAGE (V) Figure 12. SOA, Safe Operation Area



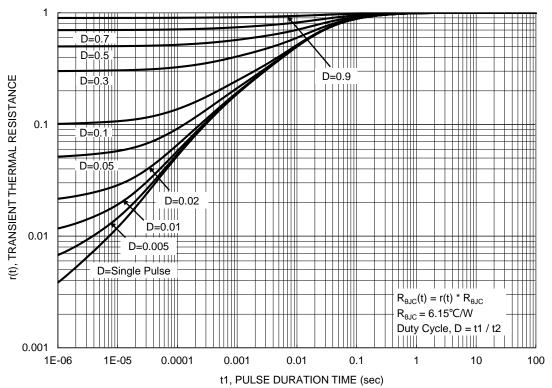


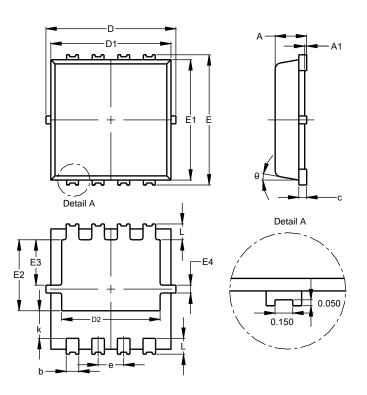
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (SWP) (Type UX)

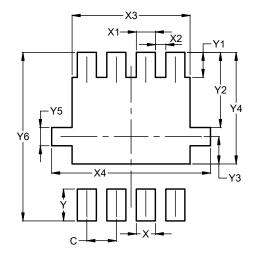


PowerDI3333-8 (SWP)					
(Type UX)					
Dim	Min	Max Ty			
Α	0.75	0.85	0.80		
A1	0.00	0.05			
b	0.25	0.40	0.32		
С	0.10	0.25	0.15		
D	3.20	3.40	3.30		
D1	2.95	3.15	3.05		
D2	2.30	2.70	2.50		
Е	3.20	3.40	3.30		
E1	2.95	3.15	3.05		
E2	1.60	2.00	1.80		
E3	0.95	1.35	1.15		
E4	0.10	0.30	0.20		
е	_	_	0.65		
k	0.50	0.90	0.70		
L	0.30	0.50	0.40		
θ	0°	12°	10°		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (SWP) (Type UX)



Dimensions	Value (in mm)
C	0.650
X	0.420
X1	0.420
X2	0.230
Х3	2.600
X4	3.500
Υ	0.700
Y1	0.550
Y2	1.650
Y3	0.600
Y4	2.450
Y5	0.400
Y6	3.700



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